



## 10N70Z

Power MOSFET

### 10A, 700V N-CHANNEL POWER MOSFET

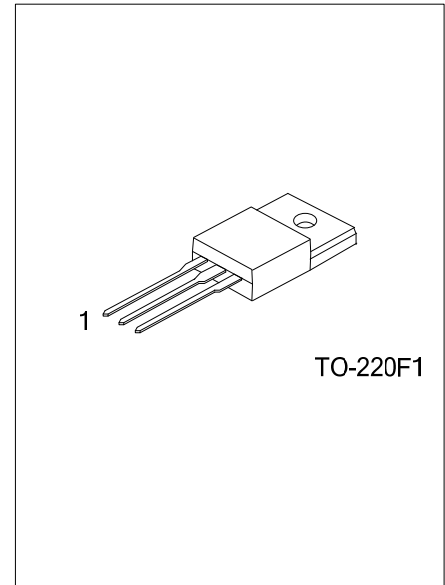
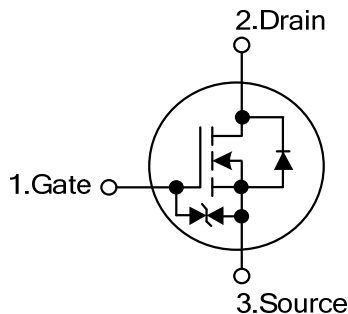
#### DESCRIPTION

The **UTC 10N70Z** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} \leq 1.2 \Omega$  @  $V_{GS}=10V$ ,  $I_D=5.0A$
- \* Low gate charge ( typical 44 nC)
- \* Low  $C_{rss}$  ( typical 18 pF)
- \* Fast switching
- \* 100% avalanche tested
- \* Improved dv/dt capability

#### SYMBOL



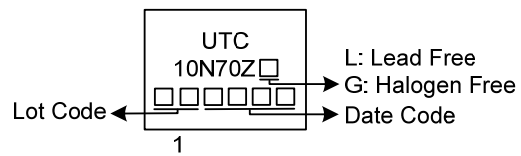
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N70ZL-TF1-T	10N70ZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N70ZG-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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## ■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	700	V
Gate-Source Voltage		$V_{GSS}$	$\pm 20$	V
Avalanche Current (Note 2)		$I_{AR}$	10	A
Drain Current	Continuous	$I_D$	10	A
	Pulsed (Note 2)	$I_{DM}$	40	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	250	mJ
	Repetitive (Note 2)	$E_{AR}$	15.6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		$P_D$	50	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Operating Temperature		$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3.  $L = 14.2\text{mH}$ ,  $I_{AS} = 10\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$  Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 9.5\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	$\theta_{JC}$	2.5	$^\circ\text{C}/\text{W}$

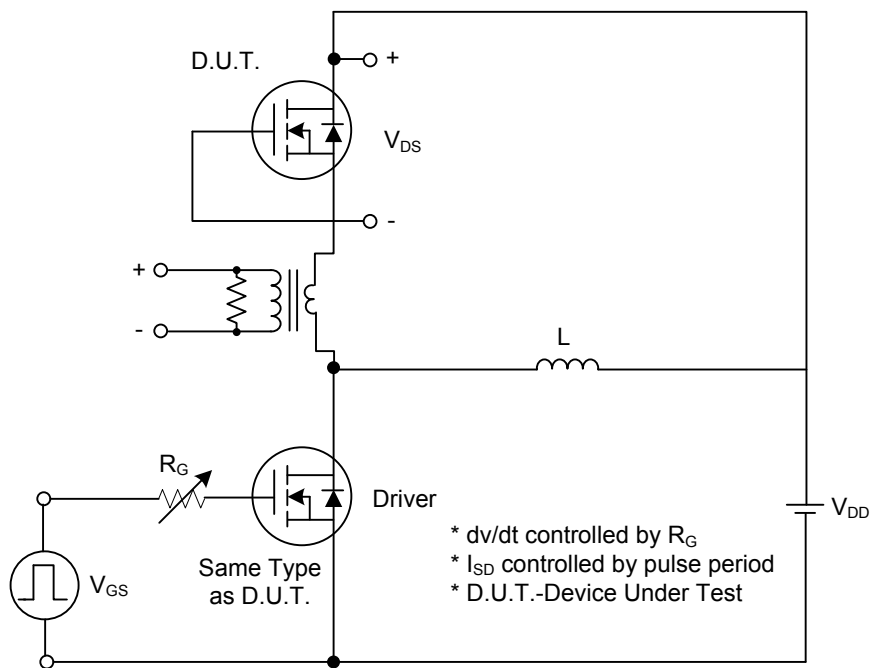
■ ELECTRICAL CHARACTERISTICS(  $T_C=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	700			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> = 700V, V <sub>GS</sub> = 0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			5	μA
	Reverse		V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-5	μA
Breakdown Voltage Temperature Coefficient		ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.0A		0.9	1.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0 MHz		1570	2040	pF
Output Capacitance		C <sub>OSS</sub>			166	215	pF
Reverse Transfer Capacitance		C <sub>RSS</sub>			18	24	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t <sub>D(ON)</sub>	V <sub>DS</sub> =350V, I <sub>D</sub> =10A, R <sub>G</sub> =25Ω (Note 1, 2)		23	55	ns
Turn-On Rise Time		t <sub>R</sub>			69	150	ns
Turn-Off Delay Time		t <sub>D(OFF)</sub>			144	300	ns
		t <sub>F</sub>			90	165	ns
Total Gate Charge		Q <sub>G</sub>	V <sub>DS</sub> =560V, I <sub>D</sub> =10A, V <sub>GS</sub> =10 V (Note 1, 2)		44	57	nC
Gate-Source Charge		Q <sub>GS</sub>			6.7		nC
Gate-Drain Charge		Q <sub>GD</sub>			18.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> =10A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I <sub>S</sub>				10	A
Maximum Pulsed Drain-Source Diode Forward Current		I <sub>SM</sub>				40	A
Reverse Recovery Time		t <sub>rr</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 10A,		420		ns
Reverse Recovery Charge		Q <sub>RR</sub>	di <sub>F</sub> / dt = 100 A/μs (Note 1)		4.2		μC

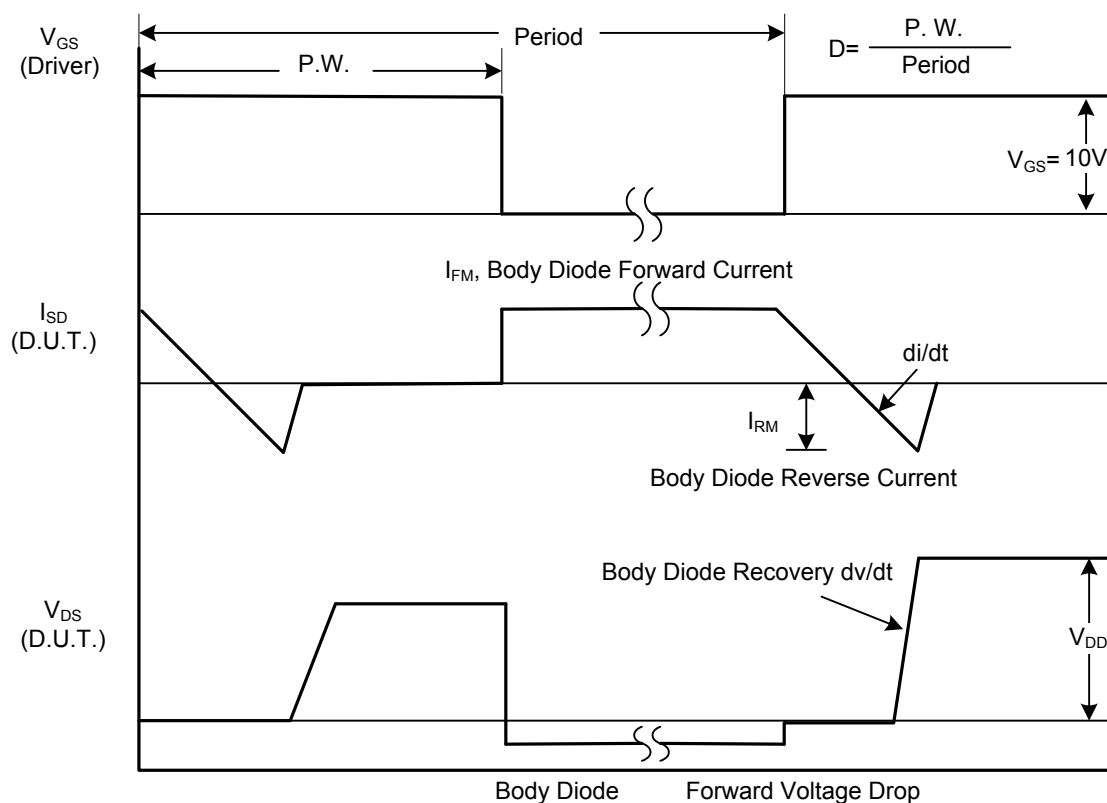
Notes: 1. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ 

2. Essentially independent of operating temperature

## ■ TEST CIRCUITS AND WAVEFORMS

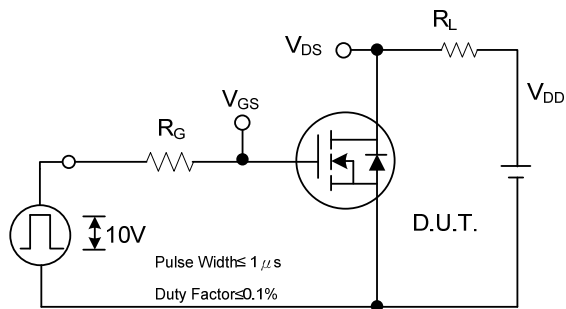


**Peak Diode Recovery dv/dt Test Circuit**

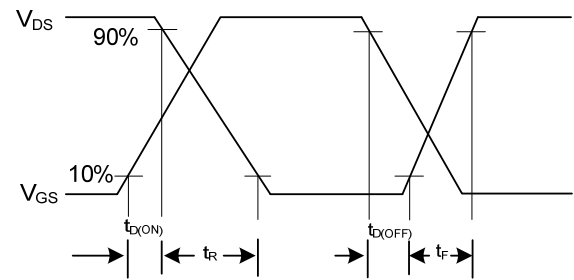


**Peak Diode Recovery dv/dt Waveforms**

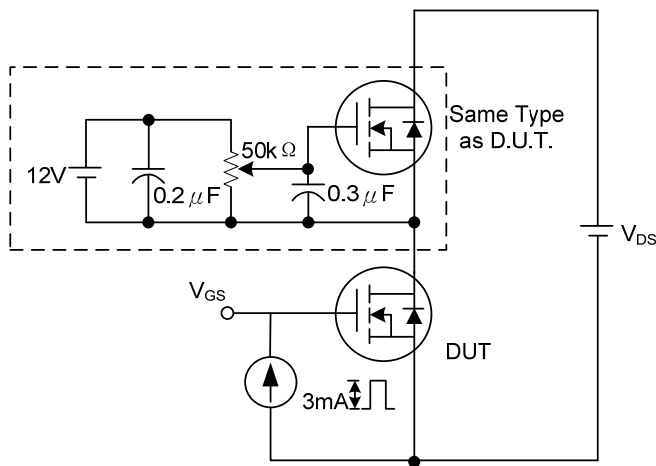
### ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



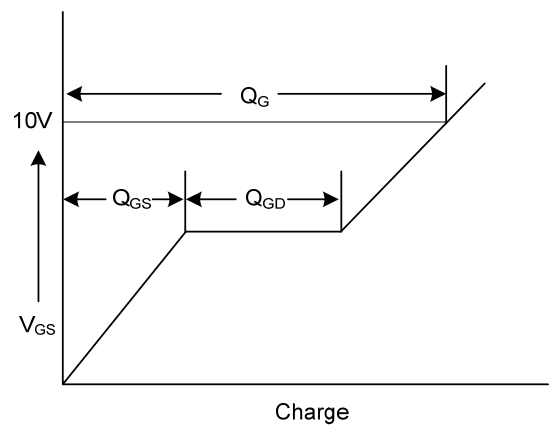
**Switching Test Circuit**



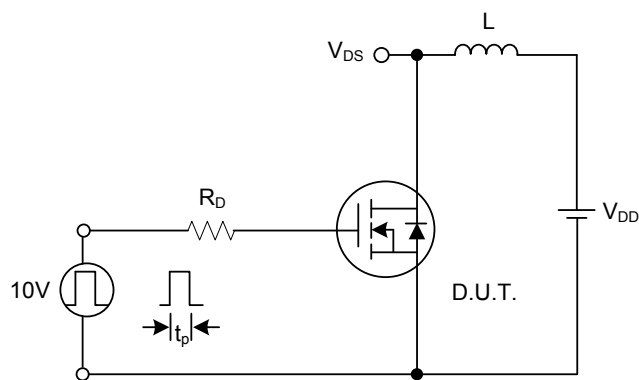
**Switching Waveforms**



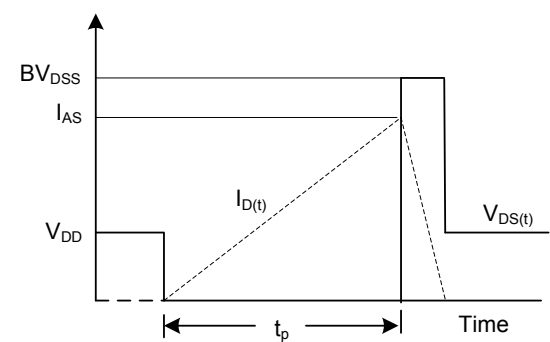
**Gate Charge Test Circuit**



**Gate Charge Waveform**

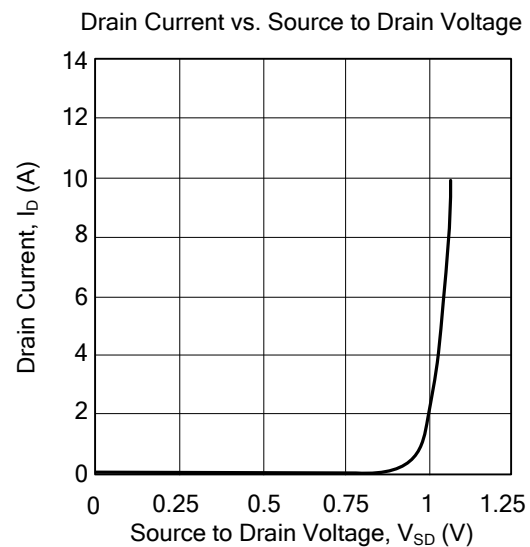
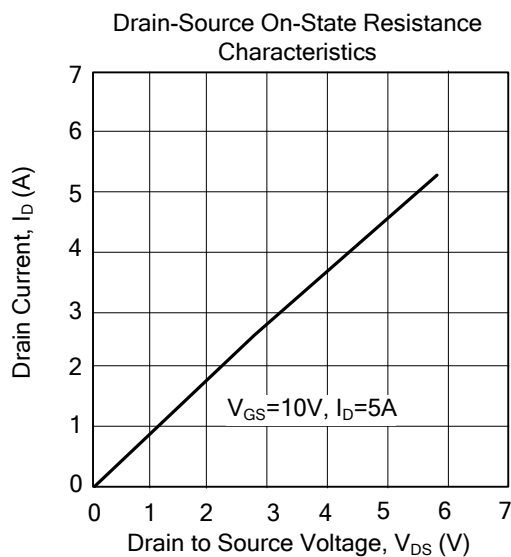
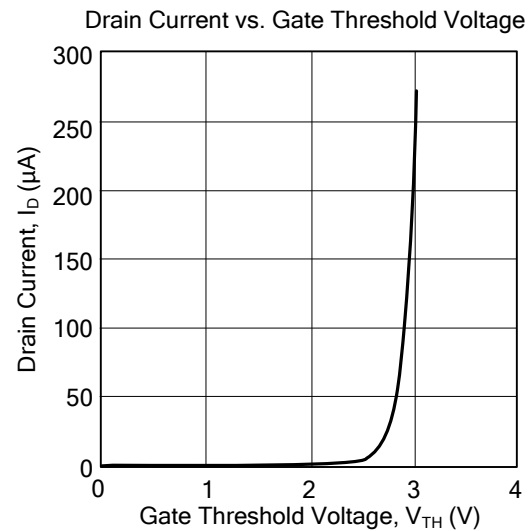
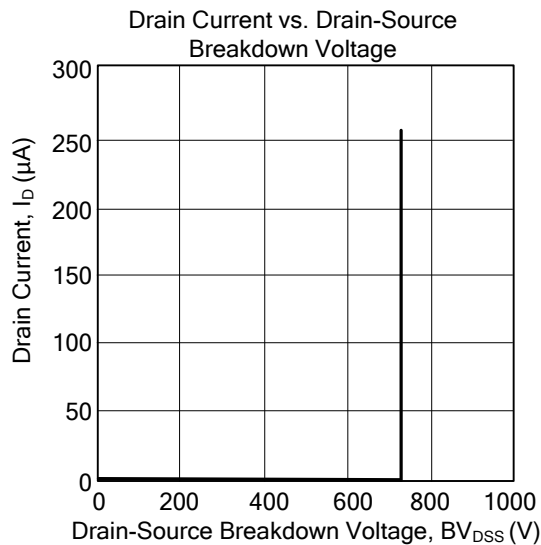


**Unclamped Inductive Switching Test Circuit**



**Unclamped Inductive Switching Waveforms**

## ■ TYPICAL CHARACTERISTICS



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